



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
0.40\/	11Ω @ V _{GS} = 10V	0.27A
240V	12Ω @ V _{GS} = 4.5V	0.26A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

Features and Benefits

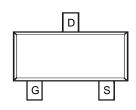
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

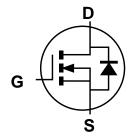
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe). Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)







Top View Pin Configuration



Equivalent Circuit

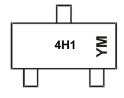
Ordering Information (Note 5)

Part Number	Case	Packaging
DMN24H11DSQ-7	SOT23	3,000/Tape & Reel
DMN24H11DSQ-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



4H1 = <u>Pr</u>oduct Type Marking Code YM <u>or YM</u> = Date Code Marking Y or Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	201	1	~		2017	20	18	2019		2020	2	2021
Code	Υ		~		Е	ı	=	G		Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	240	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 7) V _{GS} = 10V	I _D	0.27 0.22	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle ≦1%)	I _{DM}	0.8	Α		
Maximum Body Diode Continuous Current (Note 6)	Is	0.8	А		
Peak Diode Recovery dv/dt			dv/dt	6.0	V/ns

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation	(Note 6)	Б	0.75	W	
Total Fower Dissipation	(Note 7)	P_{D}	1.2		
Thermal Resistance, Junction to Ambient	(Note 6)	D	166		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	104	°C/W	
Thermal Resistance, Junction to Case	R ₀ JC	35			
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

Electrical Characteristics (@ $T_A = \pm 25$ °C, unless otherwise specified.)

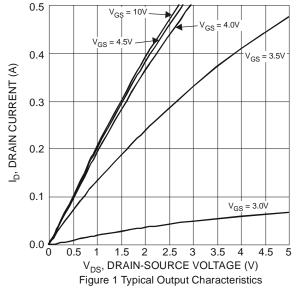
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	240	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	100	nA	V _{DS} = 240V, V _{GS} = 0V		
Gate-Body Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _{GS(TH)}	1.0	2.0	3.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
Static Drain-Source On-Resistance	D-s/s/		3.7	11	Ω	$V_{GS} = 10V, I_D = 0.3A$		
Static Dialii-Source Oil-Resistance	R _{DS(ON)}	_	4.0	12	12	$V_{GS} = 4.5V, I_D = 0.2A$		
Diode Forward Voltage	V _{SD}		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 0.1A$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C _{iss}		76.8			$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz		
Output Capacitance	Coss		6.9		pF			
Reverse Transfer Capacitance	C _{rss}	_	4.1	_				
Gate Resistance	R _G	_	17	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz		
Total Gate Charge	Qg	_	3.7	_		1201/1/		
Gate-Source Charge	Q _{gs}		0.3	_	nC	$V_{DS} = 192V, V_{GS} = 10V,$ $I_{D} = 0.1A$		
Gate-Drain Charge	Q _{gd}	_	2.1	_		ID = 0.1A		
Turn-On Delay Time	t _{D(ON)}	_	4.8	_				
Turn-On Rise Time	t _R		4.7	_		$V_{DS} = 120V, I_{D} = 0.1A,$		
Turn-Off Delay Time	t _{D(OFF)}	_	17.5	_	ns	$V_{GS} = 10V$, $R_G = 6.0\Omega$		
Turn-Off Fall Time	t _F		102.3	_		!		
Reverse Recovery Time	t _{RR}	_	45.6	_	ns	V _R = 100V, I _F = 1.0A,		
Reverse Recovery Charge	Q _{RR}	_	51.6	_	nC	di/dt = 100A/µs		

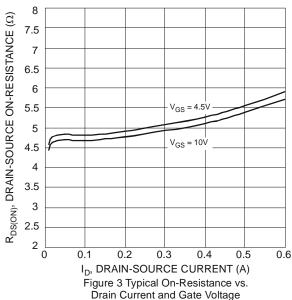
Notes:

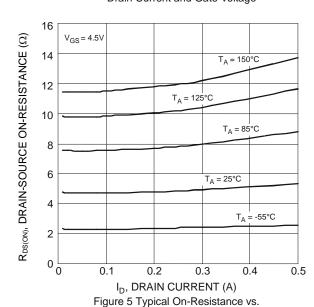
- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
- 8 .Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.



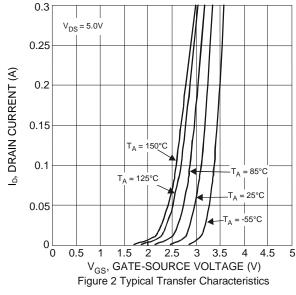


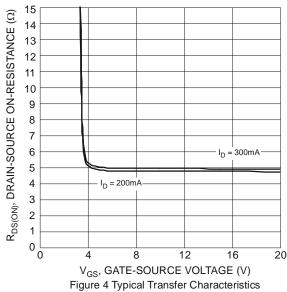






Drain Current and Temperature





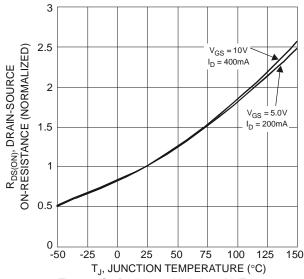
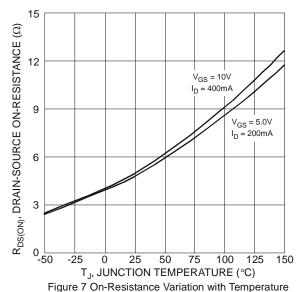
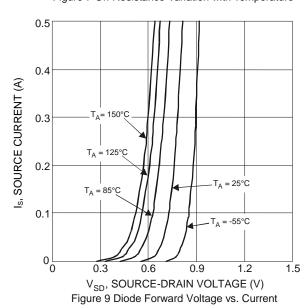


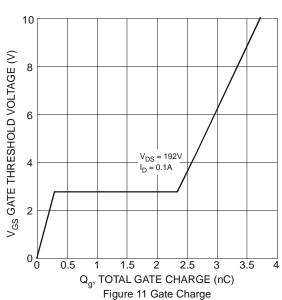
Figure 6 On-Resistance Variation with Temperature

DMN24H11DSQ









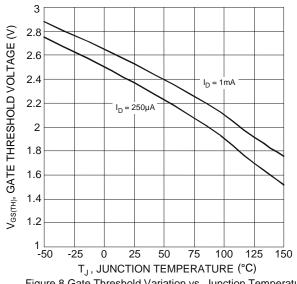
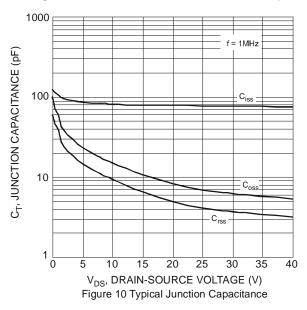
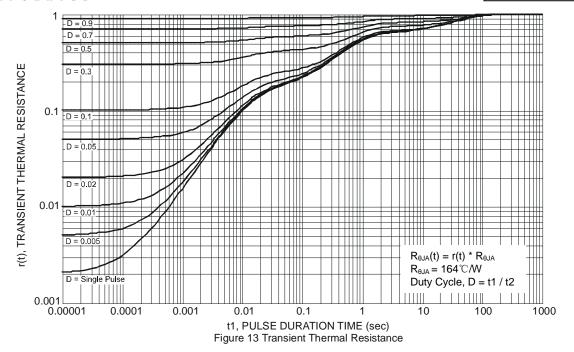


Figure 8 Gate Threshold Variation vs. Junction Temperature



R_{DS(ON)} Limited ID, DRAIN CURRENT (A) 0.01 T_{J(max)} = 150°C T_A = 25°C V_{GS} = 10V Single Pulse
DUT on 1 * MRP Board 0.001 10 100 1000 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12 SOA, Safe Operation Area



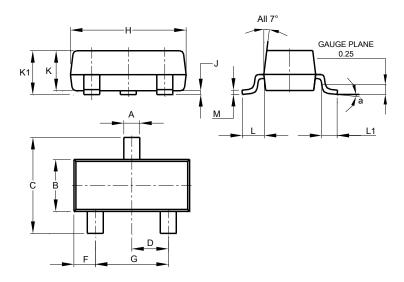




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

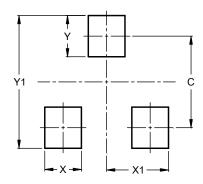


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K 1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)					
C	2.0					
Х	0.8					
X1	1.35					
Υ	0.9					
Y1	2.9					



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